EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L12	12	"349"/$.ccls. and (LCOS liquid adj crystal adj on adj silicon) same silicon adj substrate same (better durability durable flexible circuit embed embedded advantage$2 integrat$3) same glass adj substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 10:13
S1	123	349/178.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:36
S2	41	S1 and (thin adj film adj transistor or TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:40
S3	1	S2 and ferroelectric	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:41
S4	127	negative near2 dielectric near2 anisotropic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:44
S5	127	(negative near2 dielectric near2 anisotropic)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:44
S6	11	S5 and (ferroelectric ferro-electric)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 16:53
S7	6	S6 and silicon	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:45

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S8	6	S7 and color	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:45
S9	5	S8 and (indium adj tin adj oxide or ITO or indium adj zinc adj oxide or IZO)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:46
S10	5	S9 and (thin adj film adj transistor or TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:46
S11	5	S10 and inorganic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:51
S12	2	S11 and (alignment adj (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:49
S13	2	S11 and (alignment adj (film layer) or orientation adj (film layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:49
S15	2484	(chiral adj smectic adj C)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:12
S16	1558	349/149,152.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 10:25

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S17	56	349/149,152.ccls. and pad near2 region	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 13:37
S18	50	S17 and (passivation or insulat$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 09:51
S19	2	("20050088591").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 10:04
S20	4	349/149,152.ccls. and (passivation near pad)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 10:25
S21	9	("5946057" | "6097467" | "6177974").PN. OR ("6268898"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/06 10:27
S22	6	("5917572" | "6181406" | "6268898").PN. OR ("6577374"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/06 10:37
S24	96	349/149,152.ccls. and (passivation protection insulator) same pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 13:38
S25	59	349/149,152.ccls. and (passivation protection insulator) near10 pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 13:52
S26	29	349/149,152.ccls. and method same (passivation protection insulator) near10 pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 14:00

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S27	30	S25 not S26	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 13:52
S28	14	("5172212" | "5187604" | "5349205" | "5430329").PN. OR ("5581382"). URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/10/06 14:00
S29	2	S28 and method same (passivation protection insulator) near10 pad	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/06 14:00
S30	127	349/178.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 21:44
S31	2	("6682786").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/09 21:45
S32	429	"349"/$.ccls. and silicon adj substrate same glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 21:45
S33	846	"349"/$.ccls. and silicon adj substrate near8\ glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 21:45
S34	244	"349"/$.ccls. and silicon adj substrate near8 glass	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 21:48
S35	2	("20060001826").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/03/09 21:56

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S36	1035	"349"/$.ccls. and (LCOS crystal near3 silicon)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 21:57
S37	67	"349"/$.ccls. and (LCOS crystal near3 silicon) same (better durability durable flexible)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 21:58
S38	34	"349"/$.ccls. and (LCOS crystal adj on adj silicon) same (better durability durable flexible)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 21:58
S39	34	"349"/$.ccls. and (LCOS liquid adj crystal adj on adj silicon) same (better durability durable flexible)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/10 10:04
S40	53	"349"/$.ccls. and (LCOS liquid adj crystal adj on adj silicon silicon adj substrate) same (better durability durable flexible)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/09 22:00